What is claimed is:

1. A system comprising:

a high-density non-volatile fast memory; and

an ultraviolet (UV) light window adapted to expose the high-density non-volatile fast memory to UV light.

2. The system of claim 1, wherein the high-density non-volatile fast memory comprises a modified flash memory having no erasing circuitry.

3. The system of claim 1, wherein the high-density non-volatile fast memory comprises a two-terminal drain-gate-connected modified flash cell having no erasing circuitry.

4. The system of claim 3, wherein the two-terminal drain-gate-connected modified flash cell is a diode-connected nitrided read-only memory (NROM) cell.

5. A device comprising:

two-terminal drain-gate-connected modified flash cells having no erasing circuitry; and

an ultraviolet (UV) light window adapted to expose the two-terminal drain-gate-connected modified flash cells to UV light.

6. The device of claim 5, wherein the two-terminal drain-gate-connected modified flash cells are configured as a two-dimensional planar matrix of cells.

7. The device of claim 6, wherein the two-dimensional planar matrix of cells is a NAND configuration.

8. The device of claim 6, wherein the two-dimensional planar matrix of cells is a NOR configuration.

9. The device of claim 5, wherein the two-terminal drain-gate-connected modified flash cells are configured as three-dimensional layers.

10. A system comprising:

modified flash cells having no erasing circuitry; and

an ultraviolet (UV) light window adapted to expose the modified flash cells to UV light.

11. The system of claim 10, wherein the UV light window is located above a control gate of the modified flash cells.

12. The system of claim 10, wherein the UV light window is located below a substrate of the modified flash cells.

13. The system of claim 10, wherein the UV light window is interposed between control gates of the modified flash cells.

14. The system of claim 10, wherein the UV light window is offset from control gates of the modified flash cells.

15. The system of claim 10, wherein the UV light window is adapted to diffuse UV light entering the UV light window.

16. The system of claim 10, wherein the modified flash cells are arranged in a NAND configuration.

17. The system of claim 10, wherein the modified flash cells are arranged in a NOR configuration.

18. The system of claim 10, wherein the modified flash cells are configured as a two-dimensional planar matrix of cells.

19. The system of claim 18, wherein the two-dimensional planar matrix of cells is a NAND configuration.

20. The system of claim 18, wherein the two-dimensional planar matrix of cells is a NOR configuration.

21. The system of claim 10, wherein the modified flash cells are configured as three-dimensional layers.

22. The system of claim 21, wherein the three-dimensional layers comprise modified flash cells arranged in a NAND configuration.

23. The system of claim 21, wherein the three-dimensional layers comprise modified flash cells arranged in a NOR configuration.

24. The system of claim 10, further comprising an electronic device adapted to house the modified flash cells, the electronic device having an opening to receive the UV light window.

25. The system of claim 24, wherein the electronic device is a portable electronic device.

26. The system of claim 25, wherein the portable electronic device is a cellular telephone.

27. The system of claim 25, wherein the portable electronic device is a personal digital assistant (PDA).

28. The system of claim 25, wherein the portable electronic device is an MP3 player.

29. The system of claim 25, wherein the portable electronic device is a lap-top computer.

30. A method comprising:

exposing a high-density non-volatile fast memory to ultraviolet (UV) light; and

erasing the high-density non-volatile fast memory using the UV light.

31. The method of claim 30 further comprising:

passing light through a UV light window.

32. A method comprising:

exposing a modified flash cell to ultraviolet (UV) light; and

erasing the modified flash cell using the UV light.

33. A method comprising:

installing ultraviolet (UV) windows onto portable electronic devices having non-volatile memory;

passing UV light through the UV windows; and

erasing the non-volatile memory by exposing the non-volatile memory to the UV light through the UV light windows.

34. A system comprising:

means for exposing a modified flash cell to ultraviolet (UV) light; and

means for erasing the modified flash cell using the UV light.

35. A system comprising:

means for installing ultraviolet (UV) windows onto portable electronic devices having non-volatile memory; and

means for erasing the non-volatile memory by exposing the non-volatile memory to UV light through the UV light windows.